

IN THE SPECIFICATION:

The specification as amended below with replacement paragraphs shows added text with underlining and deleted text with ~~strikethrough~~.

Please REPLACE the paragraph [0005] beginning at page 1 with the following paragraph:

Furthermore, when fabricating TFTs for a liquid crystal display (LCD) device comprising a driver and pixel array by forming large silicon grains using the SLS crystallization technology, as disclosed in US patent No. 6,177,391~~6,177,301~~, characteristics of TFTs similar to the characteristics of TFTs fabricated using single crystalline silicon can be obtained, since a barrier effect of a grain boundary to a charge carrier direction is minimized in the case that the direction of an active channel is parallel to the growing direction of grains grown by the SLS crystallization method. TFT characteristics are greatly deteriorated in the case that the direction of the active channel is perpendicular to the growing direction of the grains, because a plurality of grain boundaries act as a trap of the charge carriers.